

This listing of claims replaces all prior versions and listings of claims in the application.

Claims 1 – 44 (canceled)

Claim 45 (currently amended): A chemical mechanical polishing method of planarizing a structure comprising:

providing a substrate supporting a material layer including protrusions comprising at least partially embedded copper (Cu);

forming at least one polish-stop layer on the material layer; and
polishing the material layer and the copper before ~~contracting~~ contacting the polish-stop layer,

wherein said forming of at least one polish-stop layer comprises forming said at least one polish-stop layer on an upper surface of said material layer such that a portion of the material layer and the copper extends above the polish stop layer.

Claim 46 (currently amended): A chemical mechanical polishing method of planarizing a structure comprising:

providing a substrate supporting a material layer including protrusions comprising at least partially embedded copper (Cu);

forming at least one polish-stop layer on the material layer; and
polishing the material layer and the copper before ~~contracting~~ contacting the polish-stop layer,

wherein said forming of at least one polish-stop layer comprises forming a pair of polish-stop layers on an upper surface of said material layer such that a portion of the material layer and the copper extends between and above the pair of polish-stop layers.

Claim 47 (previously presented): The method of claim 46 wherein said copper comprises a copper post.

Claim 48 (canceled)

Claim 49 (currently amended): The method of claim 39 45 wherein said polish-stop layer comprises tungsten (W).

Claim 50 (currently amended): The method of claim 39 45 wherein said polish-stop layer consists essentially of tungsten (W).

Claim 51 (currently amended): The method of claim 39 45 wherein said polishing comprises polishing the material layer and the copper in a slurry comprising an abrasive and an acid.

Claim 52 (previously presented): The method of claim 51 wherein said acid is phosphoric acid (H_2PO_4).

Claim 53 (canceled)

Claim 54 (currently amended): The method of claim 39 45 wherein said polish-stop layer consists of a material which is more resistant to polishing ~~that~~ than the material layer and the copper.

Claim 55 (new): The method of claim 45 wherein said copper comprises a copper post.

Claim 56 (new): The method of claim 46 wherein said polish-stop layer comprises tungsten (W).

Claim 57 (new): The method of claim 46 wherein said polish-stop layer consists essentially of tungsten (W).

Claim 58 (new): The method of claim 46 wherein said polishing comprises polishing the material layer and the copper in a slurry comprising an abrasive and an acid.

Claim 59 (new): The method of claim 58 wherein said acid is phosphoric acid (H_2PO_4).

Claim 60 (new): The method of claim 46 wherein said polish-stop layer consists of a material which is more resistant to polishing than the material layer and the copper.